



Form PTO 1449
(Modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

239499US2

SERIAL NO.

10/603,821

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yukio TANIGUCHI, et al.

FILING DATE

June 26, 2003

GROUP

U.S. PATENT DOCUMENTS

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	AZ		<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

3/1/05

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SHEET 1 OF 1

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	AV	Masakiyo MATSUMURA, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", Surface Science, Vol. 21, No. 5, pp. 278-287, 2000.
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	AZ	Y. SANO, et al., "HIGHLY PACKED AND ULTRA-LARGE Si GRAINS GROWN BY A SINGLE-SHOT IRRADIATION OF EXCIMER-LASER LIGHT PULSE", Department of Physical Electronics, Tokyo Institute of Technology, (8 pages)

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